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Γ	APPLICATION NO.	FIL	ING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
	10/822,804	04/13/2004		Darryl W. Peters	KOBE.0062	3039
	75	590	03/24/2006		EXAMINER	
	REED SMITH	I LLP		WEBB, GREGORY E		
	Suite 1400 3110 Fairview	Park Dri	ve		ART UNIT	PAPER NUMBER
	Falls Church, V				1751	-

DATE MAILED: 03/24/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
	1	''' '	
	10/822,804 PETERS, DARRYL		
Office Action Summary	Examiner	Art Unit	<del> </del>
	Gregory E. Webb	1751	
The MAILING DATE of this communication a Period for Reply	ppears on the cover sheet	with the correspondence address	•
A SHORTENED STATUTORY PERIOD FOR REF WHICHEVER IS LONGER, FROM THE MAILING  Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication.  If NO period for reply is specified above, the maximum statutory perions. Failure to reply within the set or extended period for reply will, by state Any reply received by the Office later than three months after the main earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUI 1.136(a). In no event, however, may od will apply and will expire SIX (6) M ute, cause the application to become	NICATION. a reply be timely filed  ONTHS from the mailing date of this communicated ABANDONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on 11	<u>August 2004</u> .	•	
,	nis action is non-final.		
3) Since this application is in condition for allow			s is
closed in accordance with the practice unde	r <i>Ex par</i> te Quayle, 1935 C	.D. 11, 453 O.G. 213.	
Disposition of Claims			
4) Claim(s) 1-26 is/are pending in the application 4a) Of the above claim(s) is/are withdrest is/are allowed.  5) Claim(s) is/are allowed.  6) Claim(s) 1-11,13,14,16-22 and 26 is/are rejection and claim(s) are subject to restriction and claim(s) are subject to restriction and claim(s) are subject to restriction.	rawn from consideration.		
Application Papers			~
9) The specification is objected to by the Exami	ner.		
10) The drawing(s) filed on is/are: a) a	ccepted or b)  objected t	o by the Examiner.	
Applicant may not request that any objection to the	* · · ·		
Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the			
Priority under 35 U.S.C. § 119			
12) ☐ Acknowledgment is made of a claim for foreign a) ☐ All b) ☐ Some * c) ☐ None of:     1. ☐ Certified copies of the priority docume 2. ☐ Certified copies of the priority docume 3. ☐ Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a limit	ents have been received.  ents have been received in  iority documents have been  eau (PCT Rule 17.2(a)).	Application No en received in this National Stage	
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/C Paper No(s)/Mail Date 804,604,404.	Paper N	v Summary (PTO-413) o(s)/Mail Date f Informal Patent Application (PTO-152)	

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## DETAILED ACTION

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- (e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) and the Intellectual Property and High Technology Technical Amendments Act of 2002 do not apply when the reference is a U.S. patent resulting directly or indirectly from an international application filed before November 29, 2000. Therefore, the prior art date of the reference is determined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

Claims 1-26 are rejected under 35 U.S.C. 102(b) as being anticipated by

Claims 1-11, 13, 14, 16-22, and 26 are rejected under 35 U.S.C. 102(e) as being anticipated by Masuda, Kaoru (US20020164873).

Concerning the claimed microstructure substrate, Masuda, Kaoru teaches the following:

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12. A process for removing residues from a semiconductor wafer comprising steps of: ashing a resist on a surface of the semiconductor wafer; and contacting the semiconductor wafer with supercritical CO.sub.2 including a compound having a hydroxyl group and a fluoride of formula NR1R2R3R4F, where R represents a hydrogen or alkyl group, so as to remove ashed resist from the semiconductor wafer.(see claim 12)

Concerning the carbon dioxide, supercritical state, additive for removing residues, inhibitor for suppressing residues and the tetramethylammoniumfluoride, Masuda, Kaoru teaches the following:

[0025] The fluoride is used as the additive to supercritical CO.sub.2 in the presence of a compound having a hydroxyl group, e.g., alcohol (such as ethanol, methanol, n-propanol, isopropanol, n-butanol and isobuthanol, phenol), glycol (such as ethylenglycol and methylenglycol and polyethylenglycol). The alcohol is preferred because it effectively dissolves or disperses the fluoride, such as TMAF, homogeneously in supercritical CO.sub.2. Among alcohol, ethanol is preferable because a larger amount of the fluoride, such as TMAF, can be dissolved in supercritical CO.sub.2 by the presence of the ethanol. The concentration of the compound in supercritical CO.sub.2 depends on the kind and concentration of the fluoride, and the kind of the residue.

Approximately, the compound is preferably included in supercritical CO.sub.2 in the range from 1 wt % to 20 wt % of the remover.

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Concerning the co-solvent for dissolving, polyhydric alcohol and the claimed alcohol, Masuda, Kaoru teaches the following:

[0022] According to the present invention, the co-solvent is added to CO.sub.2 together with the additive. The co-solvent of the present invention is a compound having an affinity to both CO.sub.2 and the additive. Such a co-solvent dissolves or disperses the additive homogeneously in the pressurized CO.sub.2 in fluid condition. An alcohol, dimethylsulfoxide or a mixture thereof is used as the co-solvent. The alcohol may be any alcohol, e.g. ethanol, methanol, n-propanol, iso-propanol, n-butanol, iso-butanol, diethyleneglycolmonomethyleter, diethyleneglycolmonoethyleter, and hexafluoro isopropanol, preferably ethanol and methanol.

Karoru fails to teach the dimethylacetamide and the propylene glycol.

Claims 1-7, 13, 14, 17-21 are rejected under 35 U.S.C. 102(b) as being anticipated by Vaartstra (US6149828).

Concerning the claimed microstructure substrate, carbon dioxide and the supercritical state, Vaartstra teaches the following:

A supercritical etching composition and method for etching an inorganic material of a semiconductor-based substrate are provided. The method

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includes providing a semiconductor-based substrate having an exposed inorganic material and exposing the substrate to the supercritical etching composition, whereby exposed inorganic material is removed from the substrate. In one embodiment, the supercritical etching composition includes a supercritical component, which is not capable of etching a particular exposed inorganic material, and a nonsupercritical etching component, which is capable of etching the particular exposed inorganic material. In another embodiment, the supercritical etching composition includes a supercritical component, which is capable of etching the particular exposed inorganic material.(par#1)

Concerning the quaternary compound, Vaartstra teaches the use of various additive including tetramethyl ammonium fluoride (see col. 6, lines 45-65)

Concerning the cosolvent, Vaartstra teaches the use of non-supercritical solvents including hexafluoroacetyl acetone (see cols. 5-6).

## Conclusion

Claims 12, 15, 23-25 are objected to for being dependent upon a rejected claim but would be allowable pending the incorporation of the limitations of the independent claim.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Gregory E. Webb whose telephone number is 571-272-1325. The examiner can normally be reached on 9:00-17:30 (m-f).

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If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Douglass McGinty can be reached on (571)272-1029. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Gregory E. Webb Primary Examiner Art Unit 1751

gew